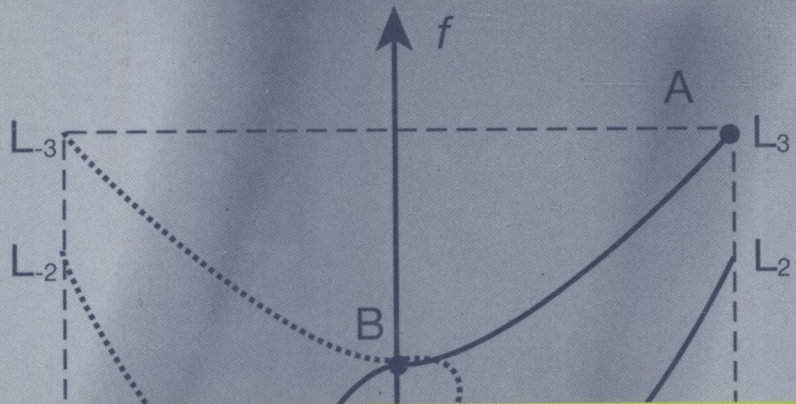
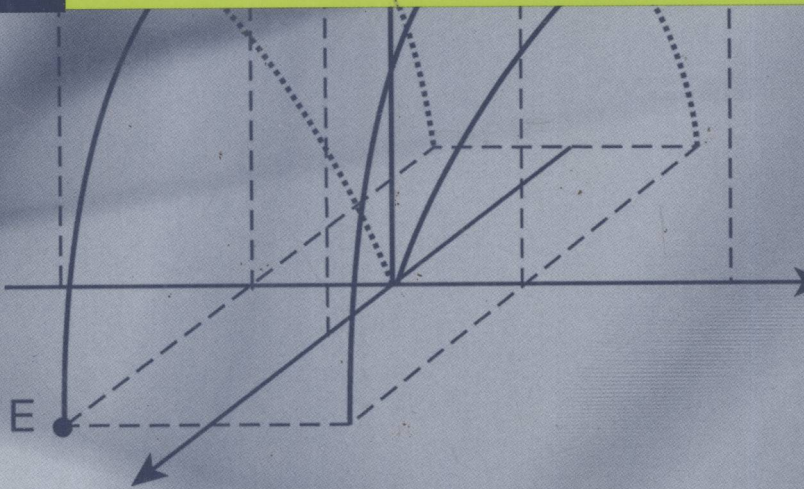


Ken-ya Hashimoto
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RF BULK ACOUSTIC WAVE FILTERS FOR COMMUNICATIONS



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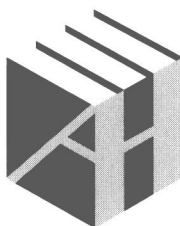
RF Bulk Acoustic Wave Filters for Communications

Ken-ya Hashimoto

Editor



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RF Bulk Acoustic Wave Filters for Communications

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Preface

Nowadays, electromechanical (EM) resonators are widely used in most sophisticated electronic equipment. For example, bulk acoustic wave (BAW) resonators using crystal quartz are indispensable for frequency or time generation owing to their outstanding performances.

The mobile communication market has grown explosively in last two decades. From a technological point of view, this growth is significantly indebted to the rapid evolution of silicon technologies, and most of all, functionalities are now realized by the use of silicon integrated circuits (Si-IC). However, highly precise frequency generation and excellent radio-frequency (RF) filtering are exceptional. They were only realizable by the use of quartz resonators and surface acoustic wave (SAW) devices, respectively.

RF-BAW devices employing a piezoelectric thin membrane were proposed in 1980. Although their excellent performance was well recognized, the majority of engineers believed that their applicability was very limited due to extremely tight requirements given to the device fabrication.

However, the tremendous efforts of a few believers moved mountains. RF-BAW devices progressed surprisingly in the last decade and are now mass produced. Furthermore, they are attempting to take over the current RF-SAW filter market.

The devices also receive much attention from Si-IC industries for their use as a core element in sophisticated RF front-end and/or one-chip radio modules based on the system-on-chip (SoC) or system-in-package (SiP) integration with active circuitry.

This book deals with key technologies and hidden know-hows necessary for the realization of high-performance RF-BAW resonators and filters. All the authors are prominent professionals in this field, and they did their best to transfer their knowledge to the younger generation. This book is invaluable not only for young engineers and students who wish to acquire this exotic technology, but also for experts who wish to further extend their knowledge. It is extremely hard for any person to prepare such a monograph solely, and only fruitful collaboration of these authors could make this difficult task possible.

By the way, the term *film bulk acoustic wave resonator* (FBAR) might be more familiar to a majority of readers. However, its use is often limited to the category of a free-standing membrane fabricated by the surface or bulk micromachining technology. Namely, the *solidly mounted BAW resonator* (SMR) employing the multi-layered reflector(s) is excluded from this category. From this reason, we follow this categorization, and the RF-BAW resonator is used as the whole set of these two categories throughout this book.

In Chapter 1, Dr. Keneth Lakin, a pioneer of the RF-BAW devices and a technical leader in this field, reviews the background and history of the RF-BAW resonators and takes readers on a virtual tour of extensive efforts that brought the technology to its current success.

In Chapter 2, Dr. Lakin gives detailed explanations on resonator and filter topologies that frequently appear in current RF-BAW technologies.

Electrical characteristics of RF-BAW device are simulated quite well by computer simulation and its use is vital in current device design. In Chapter 3, Dr. Jyrki Kaitila describes the BAW device basics, explaining the one-dimensional modeling, detailing various second effects inherent for the precise simulation, and then discussing numerical techniques and underlying physics.

In Chapter 4, Dr. Robert Aigner and Dr. Lueder Elbrecht discuss RF-BAW devices based on the solidly mounted resonator technology. First, they consider their design and then discuss their fabrication for mass production in a semiconductor fabrication environment.

In Chapter 5, Dr. Richard Ruby, the father of FBAR, reviews free-standing bulk acoustic resonators (FBARs). Dr. Ruby begins this chapter with a short history about the high obstacles that he and his group encountered, how he struggled, and how he achieved a great triumph at the last minute.

In Chapter 6, Dr. Masanori Ueda compares the RF-BAW device with the RF-SAW device from various points of view. Dr. Ueda has been involved in the research and development of both of these devices, and can evaluate them without bias.

As described before, BAW device performances can be simulated numerically fairly well. However, achievable performances are critically dependent on employed manufacturing process, especially the quality of deposited piezoelectric thin films. In Chapter 7, Dr. Sergey Mishin and Yuri Oshmiansky describe one of the most important technologies for the fabrication of RF-BAW devices, namely, deposition of high-quality thin films mandatory for realization of high-performance BAW devices.

In Chapter 8, Dr. Gernot Fattinger and Dr. Stephan Marksteiner discuss one more important factor for the realization of high-performance RF-BAW devices: namely, characterization of RF-BAW materials and devices. They also discuss the major technologies of laser probing and electrical properties.

Integration of RF-BAW devices with semiconductor circuitry is one of the most important concerns for the future in this community. In Chapter 9, Dr. Marc-Alexandre Dubois, a principal researcher of the famous MARTINA European Consortium, details monolithic integration of RF-BAW devices on Si.

In Chapter 10, Dr. A. Bart Smolders, Dr. Jan-Willem Lobeek, and Dr. Nicolaus J. Pulsford discuss the RF integration from another aspect—system-in-package (SiP) integration. They explain various technologies used in the SiP integration, demonstrate its effectiveness, and then show how the BAW technologies fit well with RF-SiP, which will be the mainstream for further RF integration.

Ken-ya Hashimoto
Editor
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Contents

Preface	ix
CHAPTER 1	
Background and History	1
1.1 BAW Technology Background	1
1.1.1 Basic Definitions	1
1.1.2 Role of Piezoelectric Materials	2
1.1.3 Transducers and Resonators	3
1.1.4 Comparisons with SAW and Plate Wave Resonators	4
1.1.5 Other Kind of Resonators	5
1.1.6 Electrical Characteristics of Piezoelectric Resonators	7
1.1.7 Technology Driving Forces	10
1.2 Thin Plate Resonators: Towards High Frequencies	11
1.2.1 Conventional Quartz Crystal Thinning	11
1.2.2 Bonded Plate Resonators	11
1.3 Composite Resonators	12
1.4 Development of Thin Films	13
1.5 Multidimensional Effects	14
1.6 Legacy Filter Topologies	15
1.6.1 Balanced Bridge Filter	15
1.6.2 Ladder Filters	16
1.6.3 Lattice Filter	17
1.6.4 Monolithic Filters	18
1.7 Some Acoustic Device and Materials Processing Legacy	18
References	19
CHAPTER 2	
Resonator and Filter Topologies	21
2.1 Plate Edge-Supported Resonators	21
2.1.1 Pothole Membrane	21
2.1.2 Pocket Membrane	24
2.1.3 Undercut Air Gap Membrane	25
2.2 Solidly Mounted Resonators	27
2.3 Electrode Metallization	29
2.4 Temperature Compensation	31
2.5 Electrically Coupled Filters	34
2.5.1 Ladder Filters	34

2.5.2	Balanced Ladder	37
2.5.3	Conventional Lattice	37
2.6	Acoustically Coupled Filters	37
2.6.1	Stacked Crystal Filter	38
2.6.2	Coupled Resonator Filter	42
2.7	Wide-Bandwidth Tuned Coupled Resonator Filters	45
2.8	Hybrid Filters	47
2.9	Summary	48
	References	48

CHAPTER 3

	BAW Device Basics	51
3.1	Thin Film Bulk Acoustic Wave Resonator	52
3.1.1	The Prototype Resonator and Piezoelectric Constitutive Relations	52
3.1.2	The Basic Parameters and Equivalent Circuit	57
3.2	Basic Physics	59
3.2.1	Wave Propagation, Transmission, Reflection, and Attenuation of Acoustic Waves	59
3.2.2	Electroacoustic Conversion	62
3.2.3	Mason Model	64
3.2.4	Dispersion Relations and Wave Modes	67
3.2.5	Resonator Design Based on Dispersion Relations	70
3.3	Device Design	74
3.3.1	Effective Coupling Coefficient	74
3.3.2	Loss Mechanisms and Q -Values	78
3.3.3	Spurious Modes	82
3.3.4	The Other Important Parameters	88
3.4	Summary	89
	References	89

CHAPTER 4

	Design and Fabrication of BAW Devices	91
4.1	Design Considerations for BAW Devices	91
4.1.1	Electromechanical Coupling Coefficient	91
4.1.2	Quality Factor	92
4.1.3	Spurious Modes	92
4.1.4	Power Handling	93
4.1.5	Temperature Coefficient of Frequency	93
4.1.6	Area Efficiency	94
4.1.7	Interconnect Losses and Parasitics	94
4.1.8	Robustness	95
4.1.9	Nonlinearities	96
4.2	Fabrication of BAW Devices	97
4.2.1	Material Selection	97
4.2.2	Fabrication of SMR Resonators and Filters	101
4.2.3	Fabrication Tolerances and Trimming	102

4.2.4	Process Controls	108
4.3	Application Space for BAW-FBAR Technology	108
4.3.1	RF Filters and Duplexers	108
4.3.2	Oscillators	112
4.3.3	Sensors	113
	References	115

CHAPTER 5

	FBAR Resonators and Filters	117
5.1	Introduction	117
5.1.1	Short History of FBAR	117
5.1.2	The Duplexer	119
5.1.3	The Package	122
5.1.4	FBAR in Context with the Rest of the World	123
5.2	FBAR Technology	124
5.2.1	Introduction	124
5.2.2	Modeling of FBARs	126
5.2.3	Method of Ascertaining Q	129
5.2.4	The Rayleigh-Lamb Modes	133
5.2.5	Apodization	137
5.2.6	Frames	140
5.2.7	Temperature-Compensated Resonators	145
5.2.8	Coupled Resonator Filters	149
5.3	FBAR Filters	150
5.3.1	Interstage Filters	150
5.3.2	The Duplexer and Multiplexers	152
5.4	Conclusions	156
	References	158

CHAPTER 6

	Comparison with SAW Devices	161
6.1	Introduction	161
6.2	Structural Comparison and Features	161
6.3	Resonator Performance and Reliability	162
6.3.1	Q -Factor	162
6.3.2	Power Durability	165
6.4	Filter Design	166
6.5	Manufacturing Process	168
6.6	Temperature Compensation Technique	168
6.7	Application Map	169
	References	170

CHAPTER 7

	Thin Films Deposition for BAW Devices	173
7.1	Most Commonly Used Piezoelectric Materials	173
7.1.1	Zinc Oxide	173
7.1.2	PZT	173

7.1.3	Aluminum Nitride	174
7.2	Methods of Deposition of Piezoelectric Films	175
7.2.1	Sputtering	175
7.2.2	Practical Aspects of the Sputter Deposition of the AlN Films	183
7.2.3	Electron Cyclotron Resonance Deposition	187
7.2.4	Ion Beam Deposition	188
7.2.5	Metalorganic Chemical Vapor Deposition	188
7.2.6	Jet Vapor Deposition	189
7.2.7	Nonvacuum Deposition	189
7.3	Metal Deposition for BAW Applications	189
7.3.1	Aluminum	191
7.3.2	Molybdenum	192
7.3.3	Tungsten	192
7.3.4	Platinum	193
7.3.5	Ruthenium	194
7.3.6	Combinations of Metals	194
	References	194

CHAPTER 8

	Characterization of BAW Devices	197
8.1	Introduction	197
8.2	Single-Layer Material Characterization	198
8.2.1	Introduction	198
8.2.2	Dielectric and Piezoelectric Layers	198
8.2.3	Metallic Layers	200
8.3	Laser Interferometry	201
8.3.1	Introduction	201
8.3.2	Measurement Setup	201
8.3.3	Evaluation of Dispersion	203
8.4	Loss Mechanisms	204
8.4.1	Introduction	204
8.4.2	Acoustic Leakage	205
8.4.3	Acoustic Leakage Through the Bragg Reflector	207
8.4.4	Laterally Leaking Waves	211
8.4.5	Electrical Losses	212
8.4.6	Viscoelastic Losses	212
8.4.7	Scattering Losses	214
8.5	Electrical Characterization	214
8.5.1	Introduction	214
8.5.2	Resonator Measurements	214
8.5.3	Filter Measurements	217
	References	219

CHAPTER 9

	Monolithic Integration	221
9.1	Introduction	221
9.2	Compatibility Issues Between IC and BAW Technologies	223

9.3	Practical Implementation	224
9.3.1	Technology Description	225
9.3.2	Filtering LNA	227
9.3.3	WCDMA RF Front-End	228
9.3.4	WLAN Oscillator	232
9.4	Conclusion	232
	Acknowledgements	233
	References	233

CHAPTER 10

	System-in-Package Integration	235
10.1	Introduction	235
10.2	Trends in Front-End Integration for Wireless Applications	235
10.2.1	Multiband, Multimode Wireless Systems	235
10.2.2	SiP Versus SoC	239
10.3	SiP Technologies	241
10.3.1	Laminate Platform	241
10.3.2	LTCC Platform	242
10.3.3	Thin Film Platform	243
10.4	SiP Design	245
10.4.1	Electromagnetic Modeling	246
10.4.2	Design Methodology	251
10.5	Test and Industrialization, Known-Good Die Concept	252
10.6	RF-SiP Examples	253
10.6.1	General Wireless Examples	253
10.6.2	Examples Including BAW	255
	References	257

	Glossary	259
	About the Author	265
	List of Contributors	266
	Index	267

Background and History

Ken Lakin

1.1 BAW Technology Background

The purpose of this chapter is to give a brief history of the development of BAW technology which is covered in technical detail in later chapters of this book. First it is necessary to define what the BAW technology is and then put the history in that context. For the purposes of this book, BAW history is interesting not so much as who did what when (that will be apparent from numerous references) but how other technologies were drawn upon to make the development of the modern thin film BAW technology possible. Microelectronics has played a key role over the years by providing materials-processing techniques previously unavailable. Review papers give an overview of thin film resonator technology [1–5].

1.1.1 Basic Definitions

The term bulk acoustic wave (BAW) refers to primary acoustic waves that propagation in the bulk of a material whose dimensions are infinite and wherein the wave occupies all of that volume. There are three possible propagation modes called the normal modes of the material. Those modes are well understood for a large number of materials whose elastic properties are known. In more practical terms, a wave in a finite three-dimensional region can only approximate the propagation characteristics of an infinite region. The first approximation required to support a BAW is that the lateral extent of the medium is much larger than the wavelength and cross-section of the wave. The practical definition of BAW is imprecise and depends on what artifacts crop up due to the finiteness of the beam. For example, a beam starting out as being of comparable dimensions to the wavelength would appear as a point source and spread widely, due to diffraction, but could be described as some complex linear combination of the normal modes. The second approximation is that the lateral extent of the wave, and therefore of the medium, is such that the wave is primarily one-dimensional but with some residual effects due to lateral finiteness. In the direction of propagation the material extent may be very finite, such as a half-wavelength thick for a resonator. Yet in such a case, dimensions will appear large in the direction of propagation because the wave bounces within the resonator between parallel surfaces maintaining its characteristics as if propagating over considerable distance. Typical average lateral dimensions might be

approximately 100 times the wavelength for resonators in filters designed for 50-ohm source and load impedances.

Whereas finiteness is a distortion imposed on BAW, other modes of propagation are uniquely tied to the finiteness of a structure. For example, waves can propagate along and be guided by a surface or at an interface. The most notable being the solid to air interface that supports surface acoustic waves (SAWs). A feature of waves is that they tend to be guided by regions of slower velocity and lower energy density. If there is a lateral deformation at or very near a surface, the material can expand perpendicular to the force (Poisson effect) out into the air region. That added degree of freedom makes the surface appear mechanically softer and as a result the SAW is confined to the surface. In the case of SAWs the material region must be just a half space with the relevant approximation that the material is sufficiently thick that the wave does not exist at any other surfaces.

If the material region is formed as a plate with two parallel surfaces, but large in lateral extent, then another set of waves, plate waves (PW), can propagate along the parallel boundaries of the plate. These waves are most pronounced when the thickness of the plate is comparable to the propagation wavelength. It turns out that such a geometrical constraint is met by a typical BAW resonator. Further, plate waves can be generated in BAW resonators and can plague high-performance BAW resonators with parasitic resonances.

Other modes of propagation are possible in the typical BAW structural approximation but PW are the most pronounced.

Since a resonator can be thought of as a confinement structure for a wave bouncing between reflecting surfaces, it is only a manner of properly generating and confining a wave to make a useful resonator. Two issues then emerge. First, how to generate the wave, and second how to confine the wave so that most of the energy is stored with a minimum amount of energy loss except on a controlled basis.

1.1.2 Role of Piezoelectric Materials

The most straight forward method of generating an acoustic wave is to use a piezoelectric material. The piezoelectric direct and inverse effects are described in general by the equations,

$$T = cS - eE \quad (1.1)$$

$$D = eS + \epsilon E \quad (1.2)$$

Here (1.1) is Hook's law of elasticity, T is stress (force per unit area), S is strain, e is the piezoelectric coefficient, c is mechanical stiffness, ϵ is permittivity, and E is the electric field. The second equation shows the contribution of mechanical strain to electric charge generation and displacement current. Accordingly, mechanical deformations and electric properties are piezoelectrically coupled.

As will be shown in subsequent chapters, the strength of the piezoelectric coupling determines the bandwidth of filters and the mechanical losses in the material will determine resonator Q and accordingly filter insertion loss.